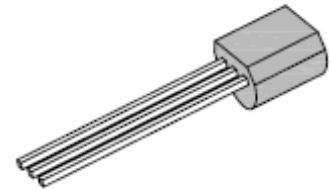


Small Signal General Purpose Transistor (NPN)

Features

- NPN Silicon Planar Transistor for Switching and Amplifier Applications
- RoHS Compliance



TO-92



Mechanical Data

| | |
|-------------------|---|
| Case: | TO-92, Plastic Package |
| Terminals: | Solderable per MIL-STD-202G, Method 208 |
| Weight: | 0.18 gram |

Maximum Ratings *(T_{Ambient}=25°C unless noted otherwise)*

| Symbol | Description | MPS5172 | Unit |
|---------------------------------------|--|-------------|-------|
| V_{CEO} | Collector-Emitter Voltage | 25 | V |
| V_{CB0} | Collector-Base Voltage | 25 | V |
| V_{EB0} | Emitter-Base Voltage | 5.0 | V |
| I_c | Collector Current Continuous | 100 | mA |
| P_D | Power Dissipation at T _A =25°C | 625 | mW |
| | Derate above 25°C | 5.0 | mW/°C |
| P_D | Power Dissipation at T _C =25°C | 1.5 | W |
| | Derate above 25°C | 12 | mW/°C |
| R_{θJA} | Thermal Resistance Junction to Ambient Air | 200 | °C/W |
| R_{θJC} | Thermal Resistance Junction to Case | 83.3 | °C/W |
| T_J, T_{STG} | Operation and Storage Junction Temperature Range | -55 to +150 | °C |

Small Signal General Purpose Transistor (NPN)

MPS5172

Electrical Characteristics ($T_{Ambient}=25^{\circ}C$ unless noted otherwise)

Off Characteristics

| Symbol | Description | Min. | Typ. | Max. | Unit | Conditions |
|------------------------|---------------------------|------|------|------|------|---|
| V_{CEO} | Collector-Emitter Voltage | 25 | - | - | V | I _C =10mA, I _B =0 |
| I_{CES} | Collector Cut-Off Current | - | - | 100 | nA | V _{CE} =50V, V _{BE} =0 |
| I_{CBO} | Collector Cut-Off Current | - | - | 100 | nA | V _{CB} =25V, I _E =0 |
| | | - | - | 10 | uA | V _{CB} =25V, I _E =0 T _a =100° C |
| I_{EBO} | Emitter Cut-Off Current | - | - | 100 | nA | V _{EB} =5V, I _C =0 |

On Characteristics

| Symbol | Description | Min. | Typ. | Max. | Unit | Conditions |
|----------------------------|---------------------------------|------|------|------|------|--|
| V_{CE(sat)} | Collector-Emitter (sat) Voltage | - | - | 0.25 | V | I _C =10mA, I _B =1.0 mA |
| V_{BE(sat)} | Base Emitter (sat) Voltage | - | 0.75 | - | V | I _C =10mA, I _B =1.0mA |
| V_{BE(on)} | Base Emitter (on) Voltage | 0.5 | - | 1.2 | V | I _C =10mA, I _B =10mA |
| *h_{FE} | D.C. Current Gain | 100 | - | 500 | | V _{CE} =10V, I _C =10mA |

*Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%

Small Signal Characteristics

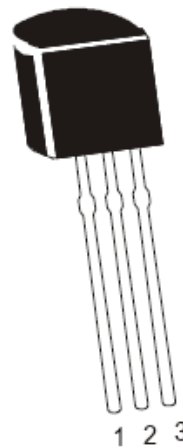
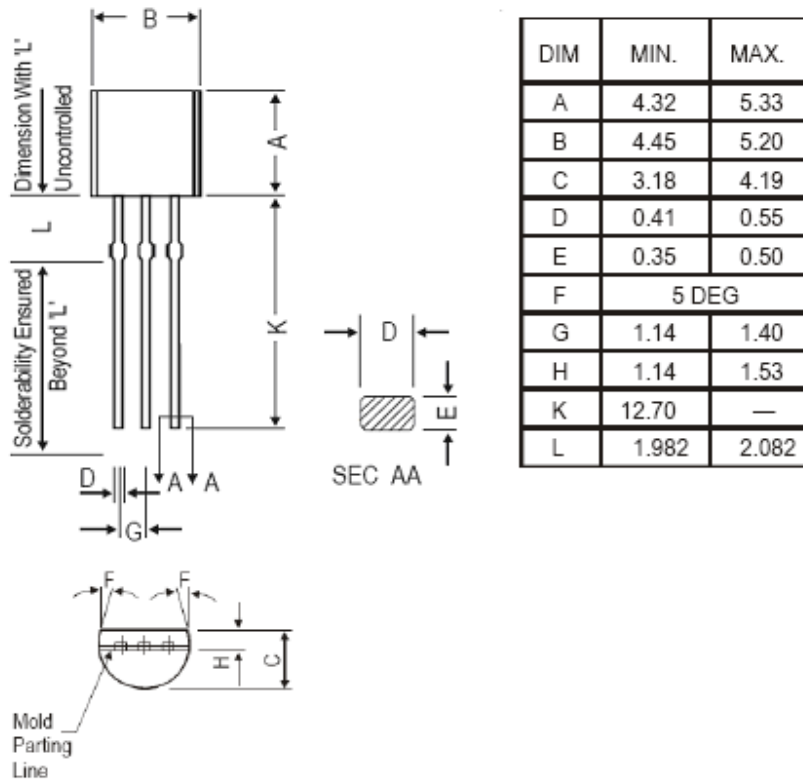
| Symbol | Description | Min. | Typ. | Max. | Unit | Conditions |
|-----------------------|--------------------------------|------|------|------|------|---|
| f_T | Current Gain-Bandwidth Product | - | 120 | - | MHz | V _{CE} =5V, I _C =2.0mA |
| C_{CB} | Collector Base Capacitance | 1.6 | - | 10 | pF | V _{CB} =0V, I _E =0 f=1MHz, |
| h_{fe} | Small Signal Current Gain | 100 | - | 750 | | V _{CE} =10V, I _C =10mA f=1KHz, |

Small Signal General Purpose Transistor (NPN)

MPS5172

Dimensions in mm

TO-92



PIN CONFIGURATION

1. EMITTER
2. BASE
3. COLLECTOR

Small Signal General Purpose Transistor (NPN)

MPS5172

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